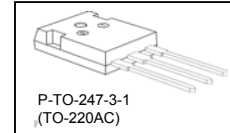
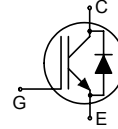


Low Loss DuoPack : IGBT in Trench and Fieldstop technology with soft, fast recovery anti-parallel EmCon HE diode

- Very low $V_{CE(sat)}$ 1.5 V (typ.)
- Maximum Junction Temperature 175 °C
- Short circuit withstand time – 5 μ s
- Designed for :
 - Frequency Converters
 - Uninterrupted Power Supply
- Trench and Fieldstop technology for 600 V applications offers :
 - very tight parameter distribution
 - high ruggedness, temperature stable behavior
 - very high switching speed
 - low $V_{CE(sat)}$
- Positive temperature coefficient in $V_{CE(sat)}$
- Low EMI
- Low Gate Charge
- Very soft, fast recovery anti-parallel EmCon HE diode
- Complete product spectrum and PSpice Models : <http://www.infineon.com/igbt/>



Type	V_{CE}	I_C	$V_{CE(sat), T_j=25^\circ C}$	$T_{j,max}$	Marking Code	Package	Ordering Code
IKW75N60T	600V	75A	1.5V	175°C	K75T60	TO-247	Q67040S4719

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CE}	600	V
DC collector current, limited by $T_{j,max}$	I_C	80 ¹	A
$T_C = 25^\circ C$		75	
$T_C = 100^\circ C$			
Pulsed collector current, t_p limited by $T_{j,max}$	I_{Cpuls}	225	
Turn off safe operating area ($V_{CE} \leq 600V, T_j \leq 175^\circ C$)	-	225	
Diode forward current, limited by $T_{j,max}$	I_F	150	
$T_C = 25^\circ C$		75	
$T_C = 100^\circ C$			
Diode pulsed current, t_p limited by $T_{j,max}$	I_{Fpuls}	225	
Gate-emitter voltage	V_{GE}	± 20	V
Short circuit withstand time ²⁾	t_{SC}	5	μ s
$V_{GE} = 15V, V_{CC} \leq 400V, T_j \leq 150^\circ C$			
Power dissipation $T_C = 25^\circ C$	P_{tot}	428	W
Operating junction temperature	T_j	-40...+175	°C
Storage temperature	T_{stg}	-55...+175	
Soldering temperature, 1.6mm (0.063 in.) from case for 10s	-	260	

¹ Value limited by bondwire

²⁾ Allowed number of short circuits: <1000; time between short circuits: >1s.

Thermal Resistance

Parameter	Symbol	Conditions	Max. Value	Unit
Characteristic				
IGBT thermal resistance, junction – case	R_{thJC}	TO-247	0.35	K/W
Diode thermal resistance, junction – case	R_{thJCD}	TO-247	0.6	
Thermal resistance, junction – ambient	R_{thJA}	TO-247 AC	40	

Electrical Characteristic, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
Static Characteristic						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0V, I_C=0.2mA$	600	-	-	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$V_{GE} = 15V, I_C=75A$ $T_j=25^\circ\text{C}$ $T_j=175^\circ\text{C}$	-	1.5	2.0	
			-	1.9	-	
Diode forward voltage	V_F	$V_{GE}=0V, I_F=75A$ $T_j=25^\circ\text{C}$ $T_j=175^\circ\text{C}$	-	1.65	2.0	
			-	1.6	-	
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C=1.2mA, V_{CE}=V_{GE}$	4.1	4.9	5.7	
Zero gate voltage collector current	I_{CES}	$V_{CE}=600V,$ $V_{GE}=0V$ $T_j=25^\circ\text{C}$ $T_j=175^\circ\text{C}$	-	-	40	μA
			-	-	1000	
Gate-emitter leakage current	I_{GES}	$V_{CE}=0V, V_{GE}=20V$	-	-	100	nA
Transconductance	g_{fs}	$V_{CE}=20V, I_C=75A$	-	41	-	S
Integrated gate resistor	R_{Gint}			-		Ω

Dynamic Characteristic

Input capacitance	C_{iss}	$V_{CE}=25V,$ $V_{GE}=0V,$ $f=1\text{MHz}$	-	4620	-	pF
Output capacitance	C_{oss}		-	288	-	
Reverse transfer capacitance	C_{riss}		-	137	-	
Gate charge	Q_{Gate}	$V_{CC}=480V, I_C=75A$ $V_{GE}=15V$	-	470	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	L_E	TO-247-3-1	-	7	-	nH
Short circuit collector current ¹⁾	$I_{C(SC)}$	$V_{GE}=15V, t_{SC}\leq 5\mu\text{s}$ $V_{CC}=400V,$ $T_j\leq 150^\circ\text{C}$	-	687.5	-	A

¹⁾ Allowed number of short circuits: <1000; time between short circuits: >1s.

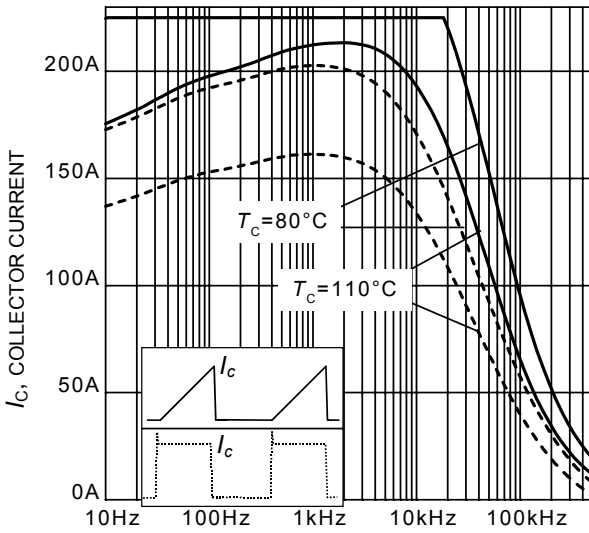
Switching Characteristic, Inductive Load, at $T_j=25^\circ\text{C}$

Parameter	Symbol	Conditions	Value			Unit	
			min.	typ.	max.		
IGBT Characteristic							
Turn-on delay time	$t_{d(on)}$	$T_j=25^\circ\text{C}$, $V_{CC}=400\text{V}$, $I_C=75\text{A}$, $V_{GE}=0/15\text{V}$, $R_G=5\Omega$, $L_{\sigma}^{1)}=100\text{nH}$, $C_{\sigma}^{1)}=39\text{pF}$ Energy losses include "tail" and diode reverse recovery.	-	33	-	ns	
Rise time	t_r		-	36	-		
Turn-off delay time	$t_{d(off)}$		-	330	-		
Fall time	t_f		-	35	-		
Turn-on energy	E_{on}		Energy losses include "tail" and diode reverse recovery.	-	2.0	-	mJ
Turn-off energy	E_{off}			-	2.5	-	
Total switching energy	E_{ts}			-	4.5	-	
Anti-Parallel Diode Characteristic							
Diode reverse recovery time	t_{rr}	$T_j=25^\circ\text{C}$, $V_R=400\text{V}$, $I_F=75\text{A}$, $di_F/dt=1460\text{A}/\mu\text{s}$	-	121	-	ns	
Diode reverse recovery charge	Q_{rr}		-	2.4	-	μC	
Diode peak reverse recovery current	I_{rrm}		-	38.5	-	A	
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	921	-	$\text{A}/\mu\text{s}$	

Switching Characteristic, Inductive Load, at $T_j=175^\circ\text{C}$

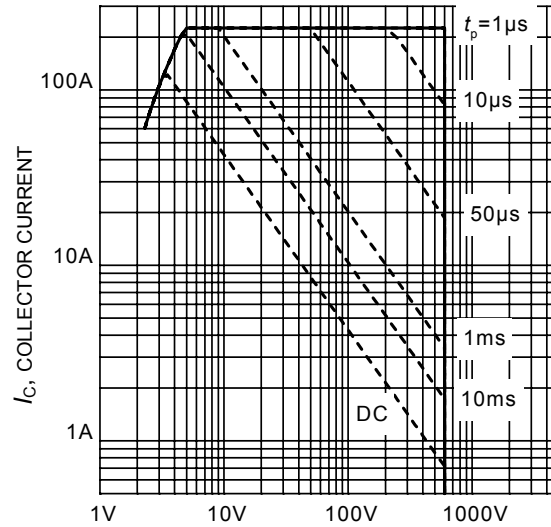
Parameter	Symbol	Conditions	Value			Unit	
			min.	typ.	max.		
IGBT Characteristic							
Turn-on delay time	$t_{d(on)}$	$T_j=175^\circ\text{C}$, $V_{CC}=400\text{V}$, $I_C=75\text{A}$, $V_{GE}=0/15\text{V}$, $R_G=5\Omega$, $L_{\sigma}^{1)}=100\text{nH}$, $C_{\sigma}^{1)}=39\text{pF}$ Energy losses include "tail" and diode reverse recovery.	-	32	-	ns	
Rise time	t_r		-	37	-		
Turn-off delay time	$t_{d(off)}$		-	363	-		
Fall time	t_f		-	38	-		
Turn-on energy	E_{on}		Energy losses include "tail" and diode reverse recovery.	-	2.9	-	mJ
Turn-off energy	E_{off}			-	2.9	-	
Total switching energy	E_{ts}			-	5.8	-	
Anti-Parallel Diode Characteristic							
Diode reverse recovery time	t_{rr}	$T_j=175^\circ\text{C}$, $V_R=400\text{V}$, $I_F=75\text{A}$, $di_F/dt=1460\text{A}/\mu\text{s}$	-	182	-	ns	
Diode reverse recovery charge	Q_{rr}		-	5.8	-	μC	
Diode peak reverse recovery current	I_{rrm}		-	56.2	-	A	
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	1013	-	$\text{A}/\mu\text{s}$	

¹⁾ Leakage inductance L_{σ} and Stray capacity C_{σ} due to dynamic test circuit in Figure E.



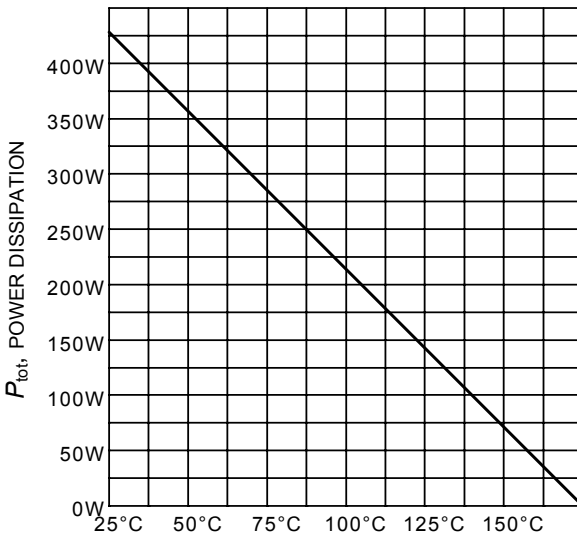
f , SWITCHING FREQUENCY

Figure 1. Collector current as a function of switching frequency
 $(T_j \leq 175^\circ\text{C}, D = 0.5, V_{CE} = 400\text{V}, V_{GE} = 0/+15\text{V}, R_G = 5\Omega)$



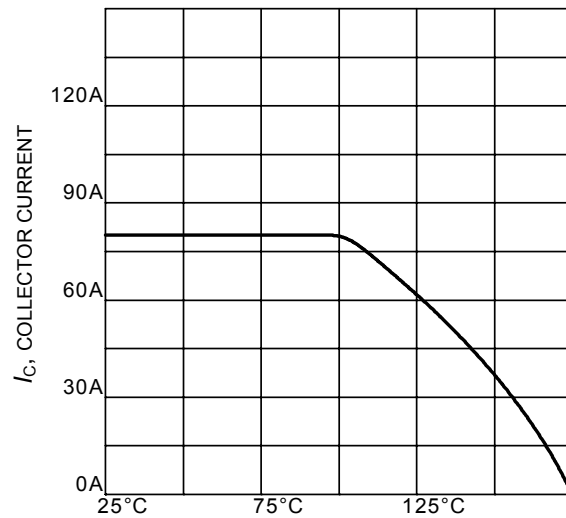
V_{CE} , COLLECTOR-EMITTER VOLTAGE

Figure 2. Safe operating area
 $(D = 0, T_C = 25^\circ\text{C}, T_j \leq 175^\circ\text{C}; V_{GE} = 15\text{V})$



T_C , CASE TEMPERATURE

Figure 3. Power dissipation as a function of case temperature
 $(T_j \leq 175^\circ\text{C})$



T_C , CASE TEMPERATURE

Figure 4. DC Collector current as a function of case temperature
 $(V_{GE} \geq 15\text{V}, T_j \leq 175^\circ\text{C})$

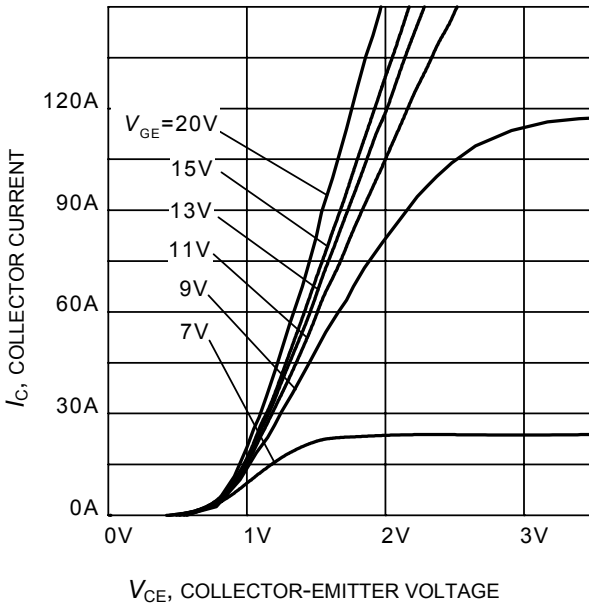


Figure 5. Typical output characteristic
($T_j = 25^\circ\text{C}$)

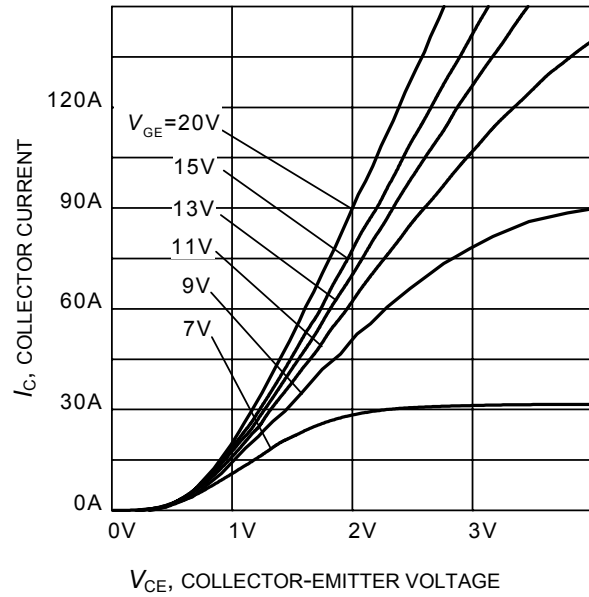


Figure 6. Typical output characteristic
($T_j = 175^\circ\text{C}$)

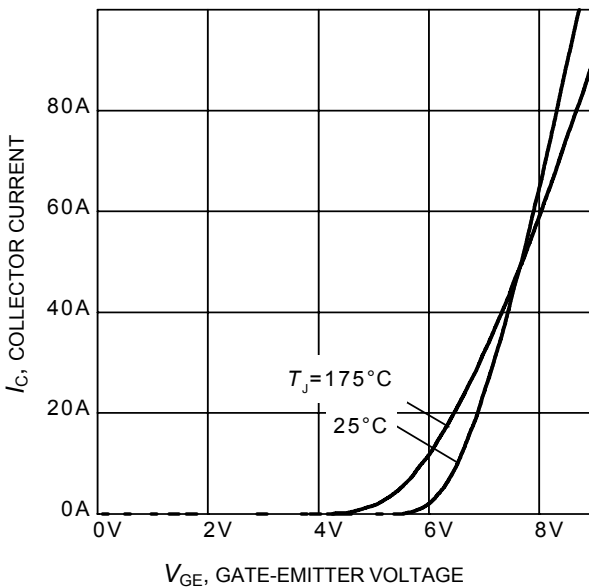


Figure 7. Typical gate transfer characteristic
($V_{CE} = 20\text{V}$)

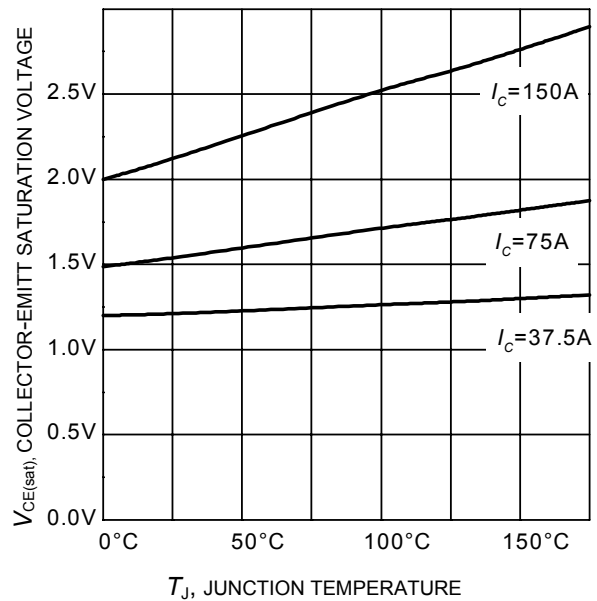


Figure 8. Typical collector-emitter saturation voltage as a function of junction temperature
($V_{GE} = 15\text{V}$)

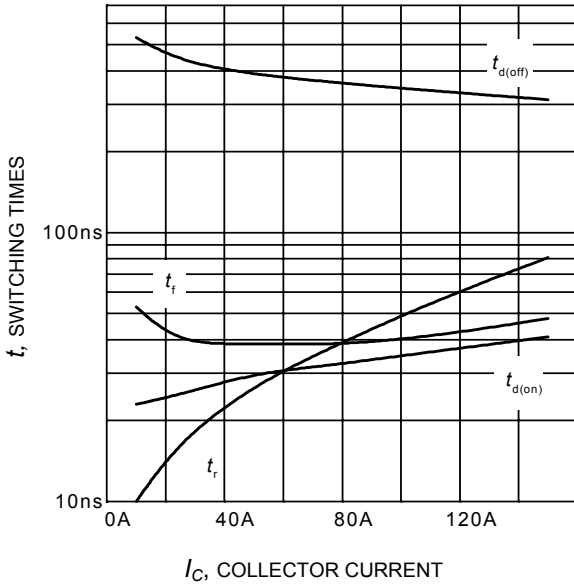


Figure 9. Typical switching times as a function of collector current
 (inductive load, $T_J=175^\circ\text{C}$,
 $V_{CE} = 400\text{V}$, $V_{GE} = 0/15\text{V}$, $R_G = 5\Omega$,
 Dynamic test circuit in Figure E)

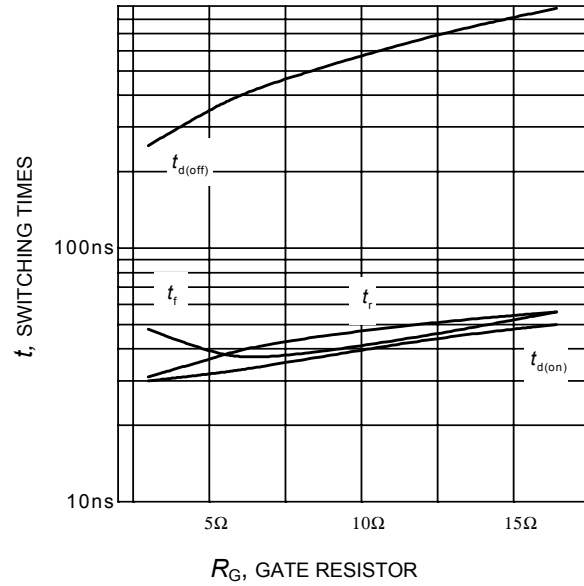


Figure 10. Typical switching times as a function of gate resistor
 (inductive load, $T_J = 175^\circ\text{C}$,
 $V_{CE} = 400\text{V}$, $V_{GE} = 0/15\text{V}$, $I_C = 75\text{A}$,
 Dynamic test circuit in Figure E)

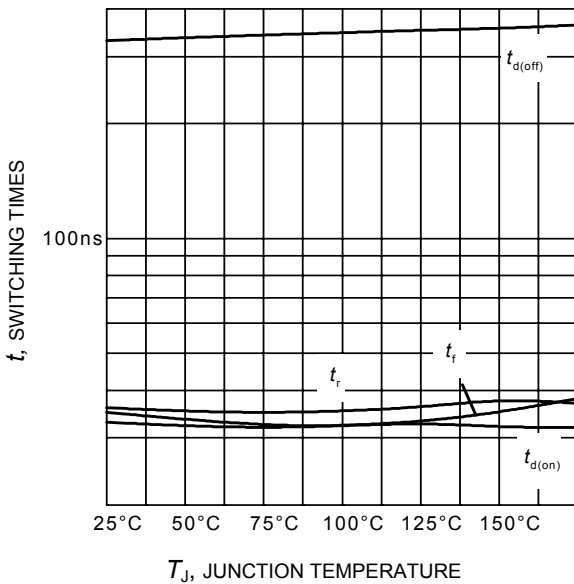


Figure 11. Typical switching times as a function of junction temperature
 (inductive load, $V_{CE} = 400\text{V}$,
 $V_{GE} = 0/15\text{V}$, $I_C = 10\text{A}$, $R_G = 5\Omega$,
 Dynamic test circuit in Figure E)

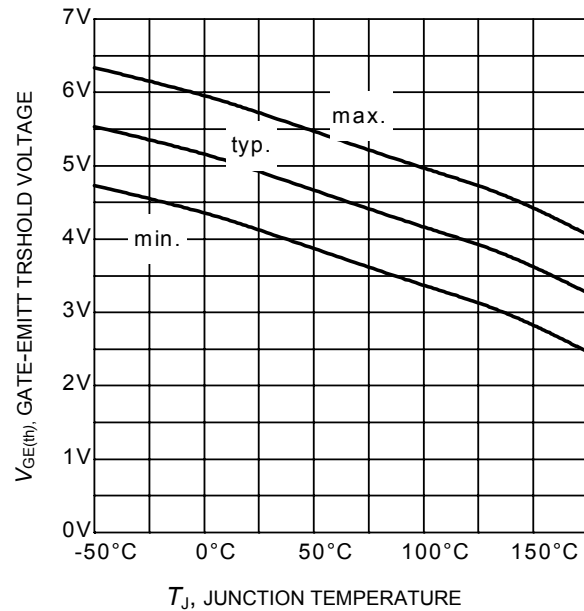


Figure 12. Gate-emitter threshold voltage as a function of junction temperature
 ($I_C = 1.2\text{mA}$)

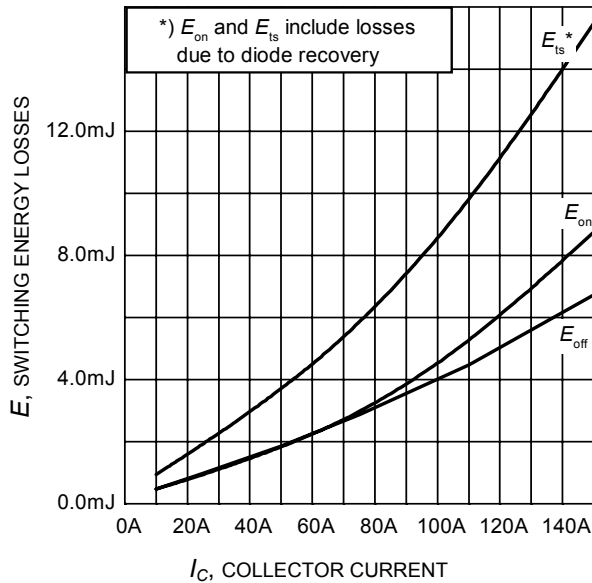


Figure 13. Typical switching energy losses as a function of collector current
 (inductive load, $T_J = 175^\circ\text{C}$,
 $V_{CE} = 400\text{V}$, $V_{GE} = 0/15\text{V}$, $R_G = 5\Omega$,
 Dynamic test circuit in Figure E)

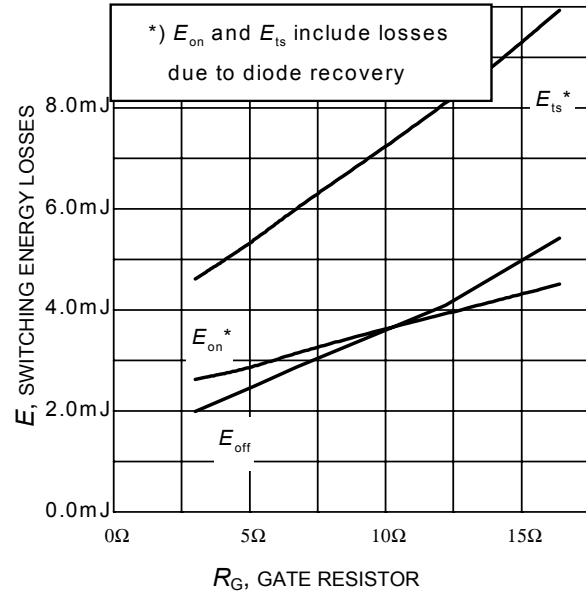


Figure 14. Typical switching energy losses as a function of gate resistor
 (inductive load, $T_J = 175^\circ\text{C}$,
 $V_{CE} = 400\text{V}$, $V_{GE} = 0/15\text{V}$, $I_C = 75\text{A}$,
 Dynamic test circuit in Figure E)

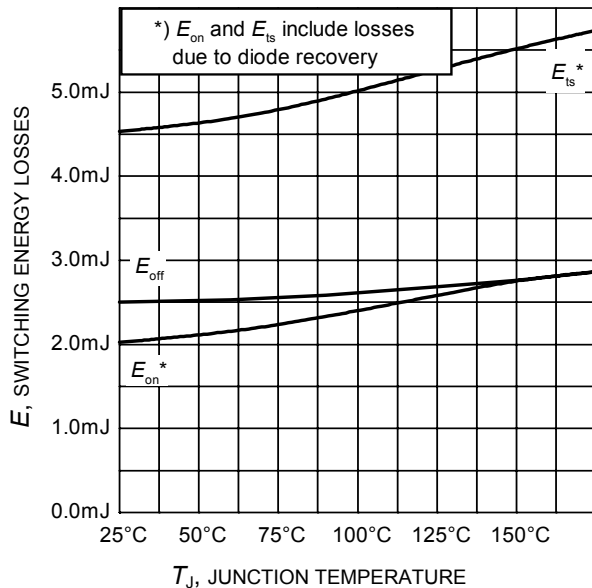


Figure 15. Typical switching energy losses as a function of junction temperature
 (inductive load, $V_{CE} = 400\text{V}$,
 $V_{GE} = 0/15\text{V}$, $I_C = 75\text{A}$, $R_G = 5\Omega$,
 Dynamic test circuit in Figure E)

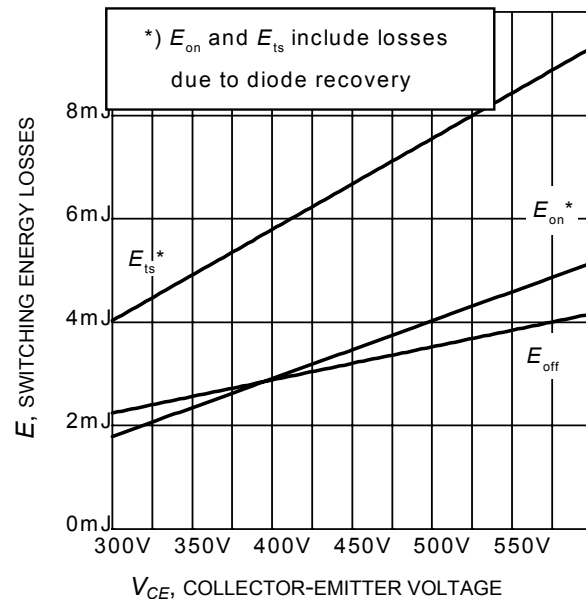


Figure 16. Typical switching energy losses as a function of collector emitter voltage
 (inductive load, $T_J = 175^\circ\text{C}$,
 $V_{GE} = 0/15\text{V}$, $I_C = 75\text{A}$, $R_G = 5\Omega$,
 Dynamic test circuit in Figure E)

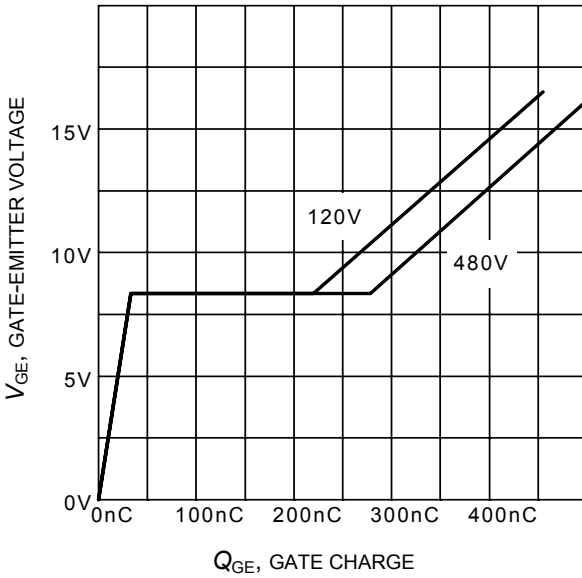


Figure 17. Typical gate charge
($I_C=75\text{ A}$)

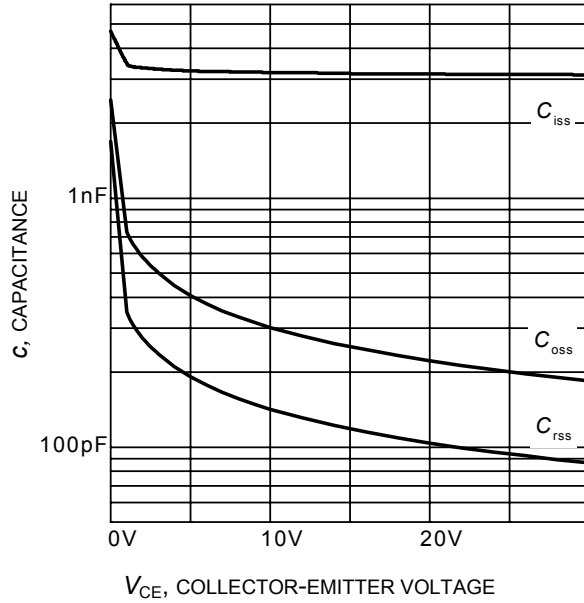


Figure 18. Typical capacitance as a function of collector-emitter voltage
($V_{GE}=0\text{V}$, $f = 1\text{ MHz}$)

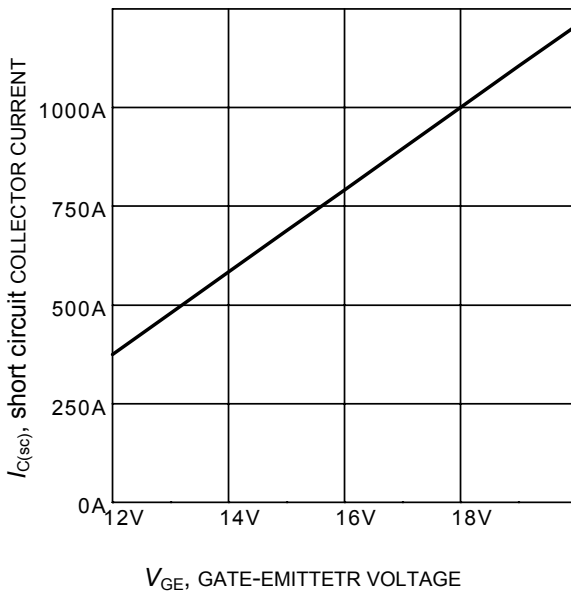


Figure 19. Typical short circuit collector current as a function of gate-emitter voltage
($V_{CE} \leq 400\text{V}$, $T_j \leq 150^\circ\text{C}$)

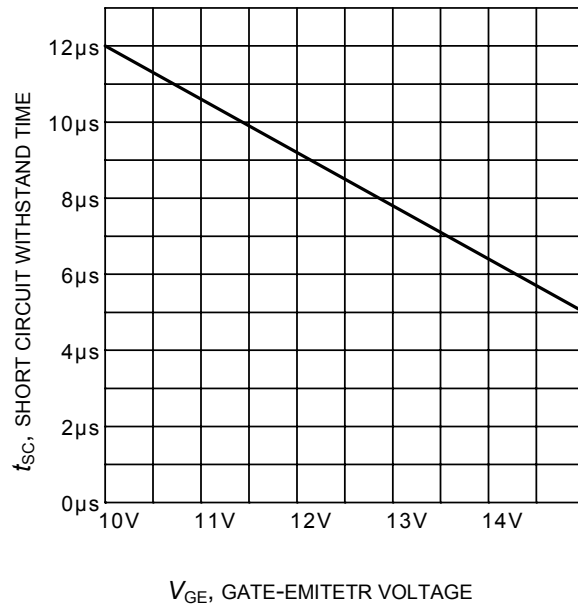


Figure 20. Short circuit withstand time as a function of gate-emitter voltage
($V_{CE}=600\text{V}$, start at $T_j=25^\circ\text{C}$, $T_{jmax}<150^\circ\text{C}$)

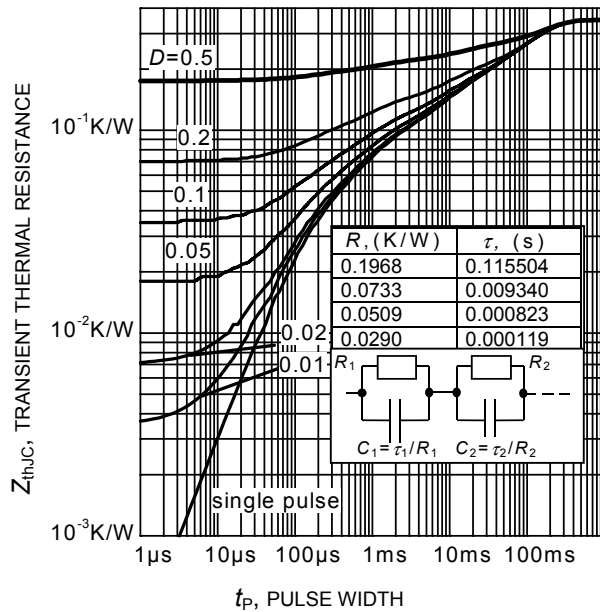


Figure 21. IGBT transient thermal resistance
($D = t_p / T$)

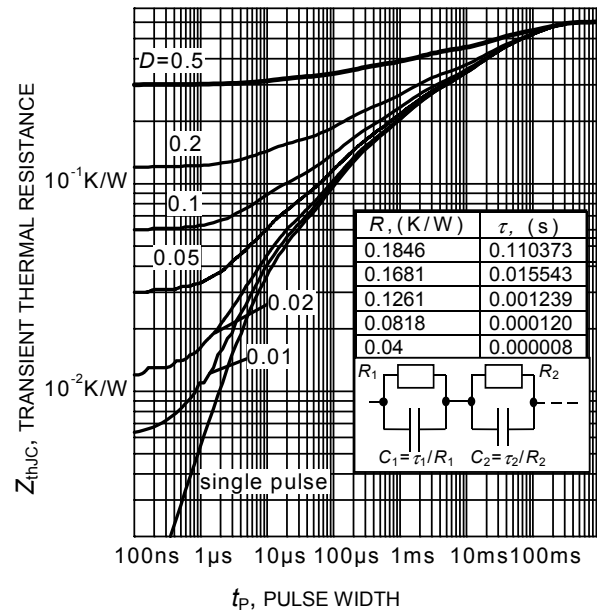


Figure 22. Diode transient thermal impedance as a function of pulse width
($D = t_p / T$)

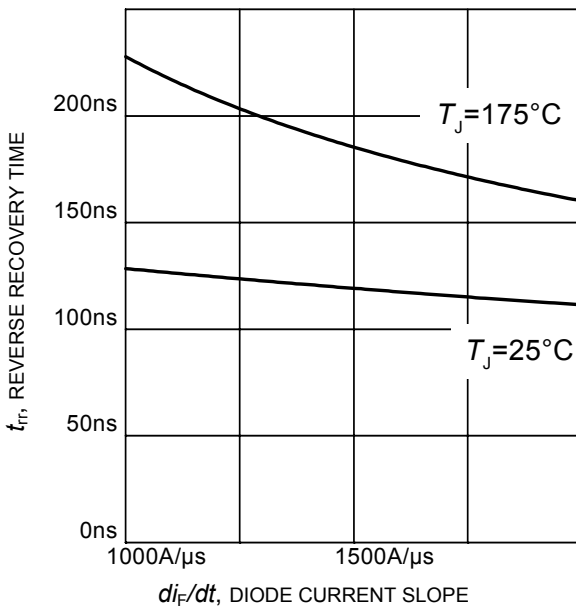


Figure 23. Typical reverse recovery time as a function of diode current slope
($V_R = 400V$, $I_F = 75A$,
Dynamic test circuit in Figure E)

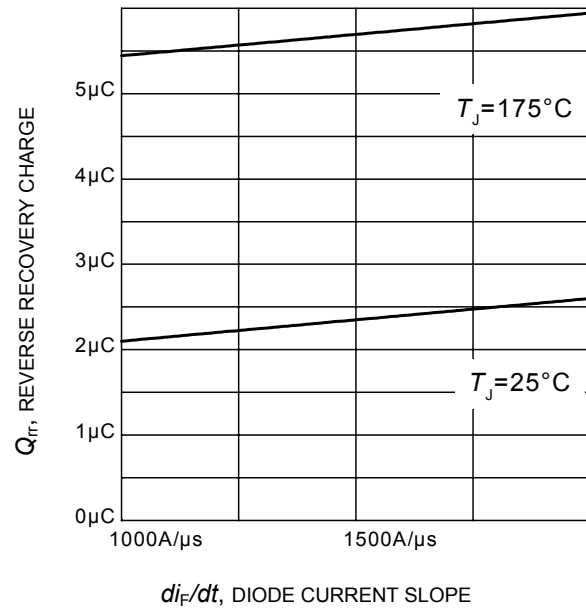
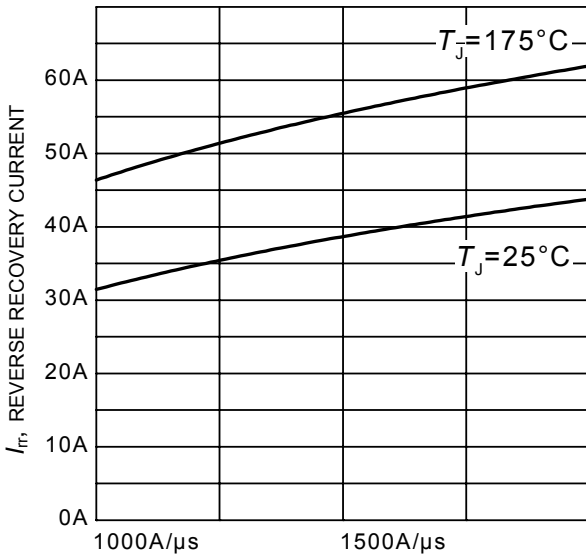


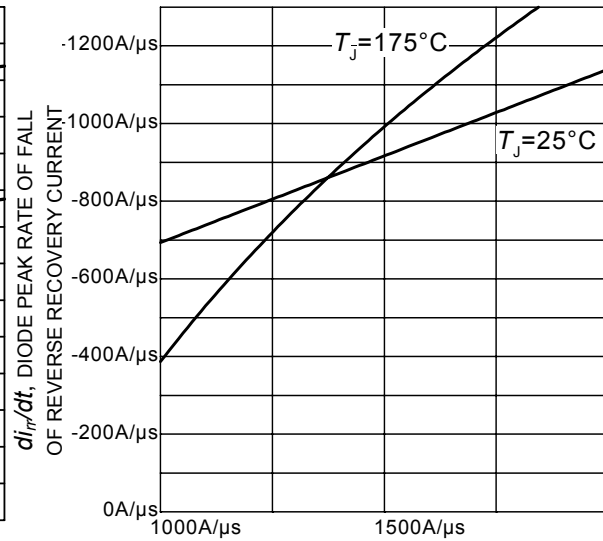
Figure 24. Typical reverse recovery charge as a function of diode current slope
($V_R = 400V$, $I_F = 75A$,
Dynamic test circuit in Figure E)



di_F/dt , DIODE CURRENT SLOPE

Figure 25. Typical reverse recovery current as a function of diode current slope

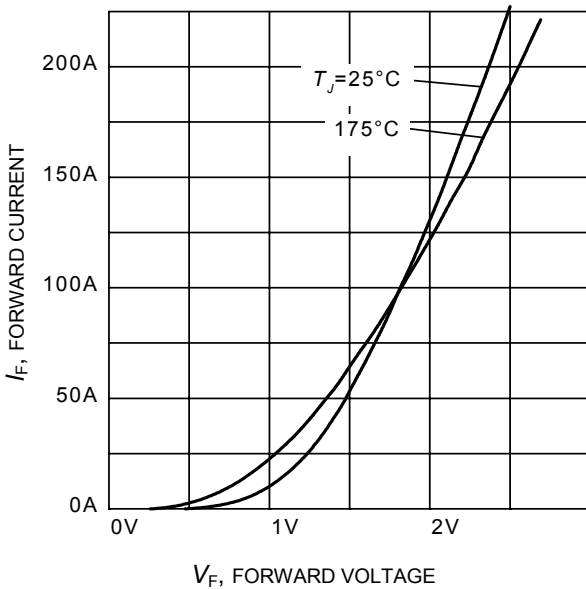
($V_R = 400V$, $I_F = 75A$,
Dynamic test circuit in Figure E)



di_F/dt , DIODE CURRENT SLOPE

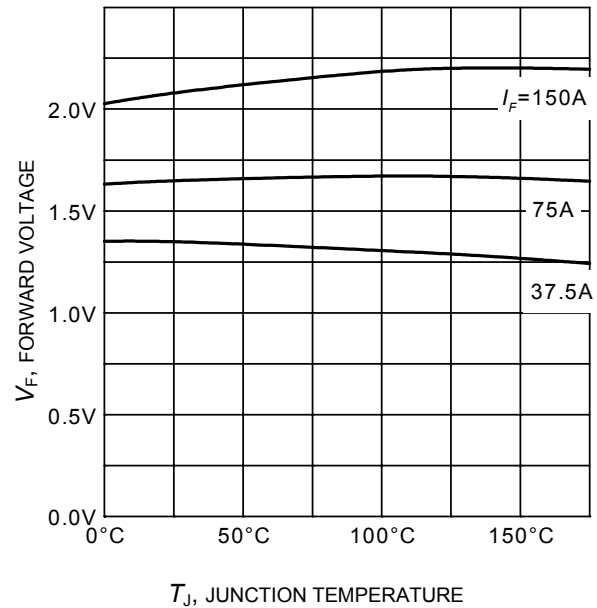
Figure 26. Typical diode peak rate of fall of reverse recovery current as a function of diode current slope

($V_R = 400V$, $I_F = 75A$,
Dynamic test circuit in Figure E)



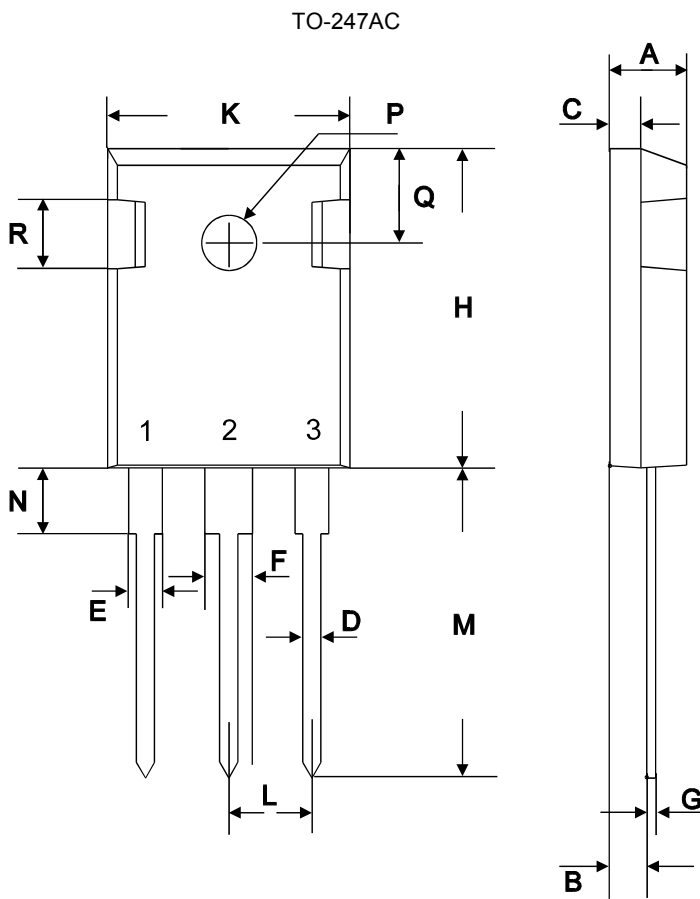
V_F , FORWARD VOLTAGE

Figure 27. Typical diode forward current as a function of forward voltage



T_J , JUNCTION TEMPERATURE

Figure 28. Typical diode forward voltage as a function of junction temperature



symbol	dimensions			
	[mm]		[inch]	
	min	max	min	max
A	4.78	5.28	0.1882	0.2079
B	2.29	2.51	0.0902	0.0988
C	1.78	2.29	0.0701	0.0902
D	1.09	1.32	0.0429	0.0520
E	1.73	2.06	0.0681	0.0811
F	2.67	3.18	0.1051	0.1252
G	0.76 max		0.0299 max	
H	20.80	21.16	0.8189	0.8331
K	15.65	16.15	0.6161	0.6358
L	5.21	5.72	0.2051	0.2252
M	19.81	20.68	0.7799	0.8142
N	3.560	4.930	0.1402	0.1941
∅P	3.61		0.1421	
Q	6.12	6.22	0.2409	0.2449

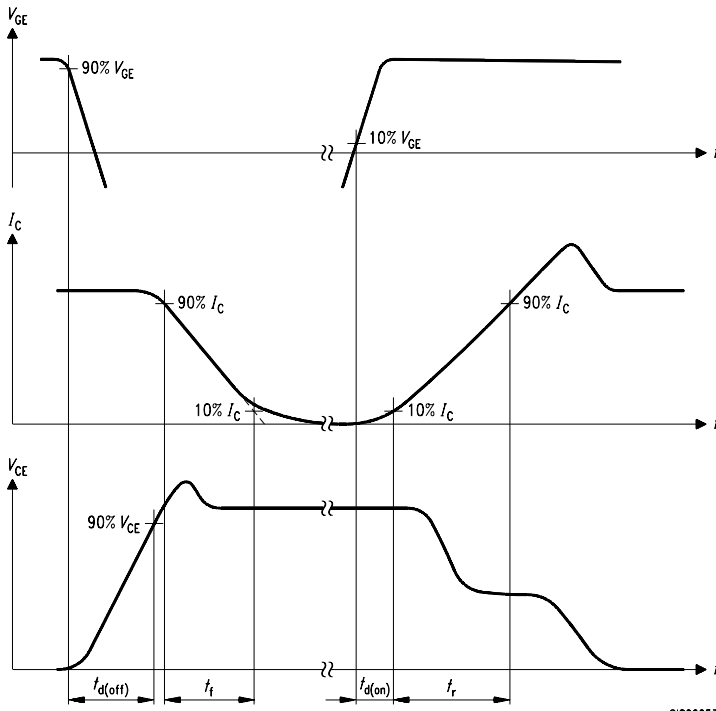


Figure A. Definition of switching times

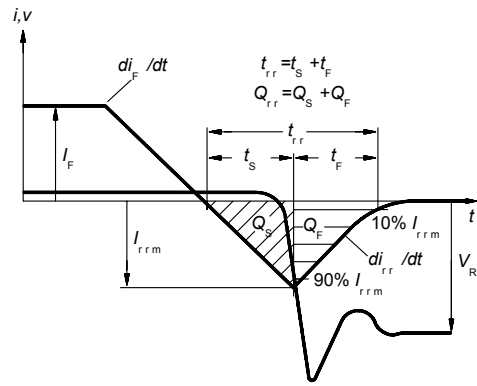


Figure C. Definition of diodes switching characteristics

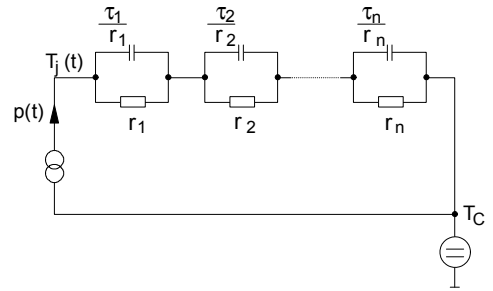


Figure D. Thermal equivalent circuit

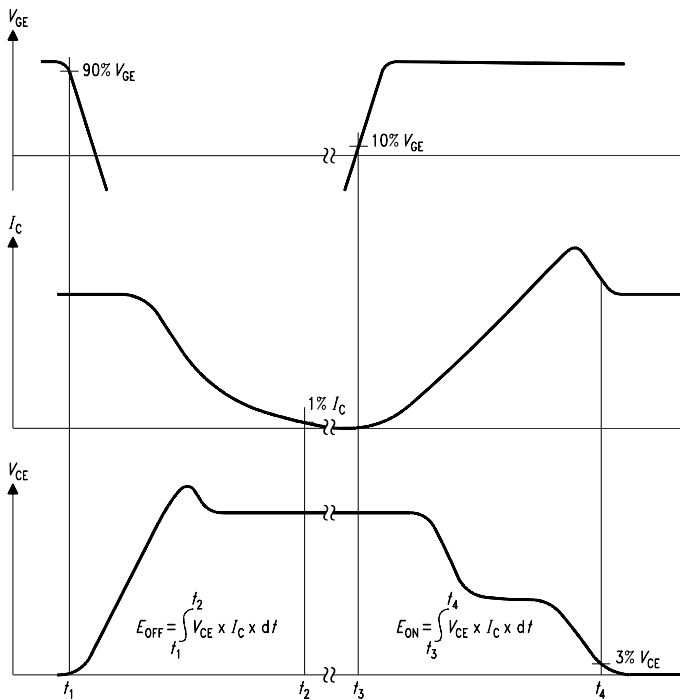


Figure B. Definition of switching losses

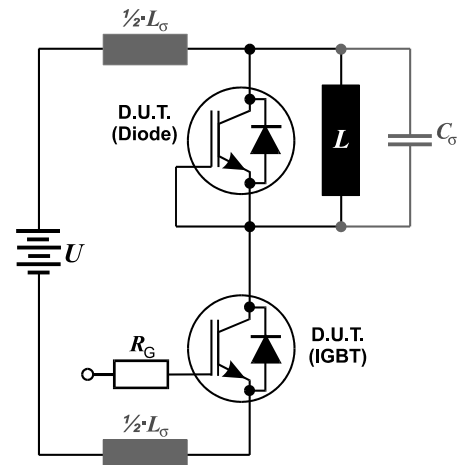


Figure E. Dynamic test circuit

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